

Peter J Parbrook

List of Publications by Year in descending order

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195
papers

3,702
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147566

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182168

51
g-index

197
all docs

197
docs citations

197
times ranked

3080
citing authors

#	ARTICLE	IF	CITATIONS
1	Micro-LED Light Emitting Diode: From Chips to Applications. Laser and Photonics Reviews, 2021, 15, 2000133.	4.4	108
2	Quantification of Trace-Level Silicon Doping in Al _x Ga _{1-x} N Films Using Wavelength-Dispersive X-Ray Microanalysis. Microscopy and Microanalysis, 2021, 27, 696-704.	0.2	1
3	A systematic comparison of polar and semipolar Si-doped AlGa _N alloys with high AlN content. Journal Physics D: Applied Physics, 2021, 54, 035302.	1.3	9
4	Tailoring Wettability Properties of GaN Epitaxial Layers through Surface Porosity Induced during CVD Deposition. Langmuir, 2021, 37, 14622-14627.	1.6	4
5	Bandgap and refractive index estimates of InAlN and related nitrides across their full composition ranges. Scientific Reports, 2020, 10, 16205.	1.6	20
6	The 2020 UV emitter roadmap. Journal Physics D: Applied Physics, 2020, 53, 503001.	1.3	289
7	Carrier dynamics near a crack in GaN microwires with AlGa _N multiple quantum wells. Applied Physics Letters, 2020, 117, .	1.5	10
8	Polarization fields in semipolar (202 Å ⁻¹ Å ⁻¹) and (202 Å ⁻¹ 1) InGa _N light emitting diodes. Applied Physics Letters, 2020, 116, 062106.	1.5	0
9	Reduction of threading dislocation density in top-down fabricated GaN nanocolumns via their lateral overgrowth by MOCVD. Journal of Applied Physics, 2020, 127, .	1.1	7
10	Thermal Stability of Crystallographic Planes of GaN Nanocolumns and Their Overgrowth by Metal Organic Vapor Phase Epitaxy. Crystal Growth and Design, 2020, 20, 3686-3700.	1.4	5
11	InAlN-based LEDs emitting in the near-UV region. Japanese Journal of Applied Physics, 2019, 58, SCCB33.	0.8	13
12	Multi-wavelength emission from a single InGa _N /Ga _N nanorod analyzed by cathodoluminescence hyperspectral imaging. Scientific Reports, 2018, 8, 1742.	1.6	9
13	Fast Growth of Smooth AlN in a 3-Å Showerhead-Type Vertical Flow MOVPE Reactor. Physica Status Solidi (B): Basic Research, 2018, 255, 1700472.	0.7	2
14	Significant contribution from impurity-band transport to the room temperature conductivity of silicon-doped AlGa _N . Journal Physics D: Applied Physics, 2018, 51, 06LT01.	1.3	9
15	In Al _{1-x} N/Al _{0.53} Ga _{0.47} N multiple quantum wells on Al _{0.5} Ga _{0.5} N buffer with variable in-plane lattice parameter. Journal of Luminescence, 2018, 194, 797-802.	1.5	3
16	Ag colloids and arrays for plasmonic non-radiative energy transfer from quantum dots to a quantum well. Nanotechnology, 2017, 28, 115401.	1.3	14
17	Doping of III-nitride materials. Materials Science in Semiconductor Processing, 2017, 62, 180-191.	1.9	81
18	Highly-Ordered Growth of Solution-Processable ZnO for Thin Film Transistors. ECS Transactions, 2017, 77, 99-107.	0.3	0

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19	Optical Reflectivity of Spin-Coated Multilayered ZnO and Al:ZnO Thin Films. ECS Transactions, 2017, 77, 75-82.	0.3	0
20	GaN Nanowire Schottky Barrier Diodes. IEEE Transactions on Electron Devices, 2017, 64, 2283-2290.	1.6	17
21	Design considerations of vertical GaN nanowire Schottky barrier diodes. , 2017, , .		0
22	Solution processed ZnO homogeneous quasisuperlattice materials. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, 061517.	0.9	3
23	Optical and structural characterisation of epitaxial nanoporous GaN grown by CVD. Nanotechnology, 2017, 28, 375701.	1.3	7
24	Influence of plasmonic array geometry on non-radiative energy transfer from a quantum well to a quantum dot layer. , 2017, , .		0
25	(Invited) Simulation Study of High Voltage Vertical GaN Nanowire Field Effect Transistors. ECS Transactions, 2017, 80, 69-85.	0.3	6
26	Enhancing Förster nonradiative energy transfer via plasmon interaction. , 2016, , .		1
27	A comparison of the ⁶⁰ Co gamma radiation hardness, breakdown characteristics and the effect of SiN _x capping on InAlN and AlGa _N HEMTs for space applications. Semiconductor Science and Technology, 2016, 31, 025008.	1.0	6
28	Exciton localization in semipolar (112̂ ⁻²) InGa _N multiple quantum wells. Journal of Applied Physics, 2016, 120, 055705.	1.1	2
29	Modeling and simulation of bulk gallium nitride power semiconductor devices. AIP Advances, 2016, 6, .	0.6	52
30	Role of substrate quality on the performance of semipolar (112̂ ⁻²) InGa _N light-emitting diodes. Journal of Applied Physics, 2016, 120, .	1.1	8
31	Strongly nonparabolic variation of the band gap in In _x Al _{1-x} N with low indium content. Semiconductor Science and Technology, 2016, 31, 025006.	1.0	12
32	Silicon doping of semipolar $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0031.gif" overflow="scroll" \rangle \langle \text{mml:mrow} \langle \text{mml:mo stretchy="true" \rangle \langle \text{mml:mn} \rangle 11 \langle \text{mml:mn} \rangle \langle \text{mml:mover} \rangle \text{Tj ETQqO O O rgBT /Overlock 10 Tf 50 222 Td (accent="true" \rangle \langle \text{mml:subscriptshift="65%" \rangle \langle \text{mml:mrow} \langle \text{mml:mi} \rangle \text{Al} \langle \text{mml:mi} \rangle \langle \text{mml:mrow} \langle \text{mml:mi} \rangle \text{x} \langle \text{mml:mi} \rangle \langle \text{mml:mrow} \langle \text{mml:msub} \rangle$	0.7	14
33	High Bandwidth Freestanding Semipolar (11̂ ⁻²²) InGa _N /Ga _N Light-Emitting Diodes. IEEE Photonics Journal, 2016, 8, 1-8.	1.0	18
34	Polar and semipolar (112) InAlN layers grown on AlN templates using MOVPE. Physica Status Solidi (B): Basic Research, 2016, 253, 99-104.	0.7	5
35	Composition dependence of photoluminescence properties of In _x Al _{1-x} N/AlGa _N quantum wells. Journal Physics D: Applied Physics, 2016, 49, 385105.	1.3	7
36	Influence of plasmonic array geometry on energy transfer from a quantum well to a quantum dot layer. Nanoscale, 2016, 8, 18170-18179.	2.8	13

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37	Self-Healing Thermal Annealing: Surface Morphological Restructuring Control of GaN Nanorods. Crystal Growth and Design, 2016, 16, 6769-6775.	1.4	10
38	Thermal modelling of transferable bonded thin film gallium arsenide laser diode. IET Optoelectronics, 2016, 10, 51-56.	1.8	4
39	Effect of V/III ratio on the growth of AlGaIn by metalorganic vapour phase epitaxy. Journal of Crystal Growth, 2016, 435, 12-18.	0.7	22
40	Development of semipolar (11-22) LEDs on GaN templates. Proceedings of SPIE, 2016, , .	0.8	8
41	Site controlled red-yellow-green light emitting InGaIn quantum discs on nano-tipped GaN rods. Nanoscale, 2016, 8, 11019-11026.	2.8	12
42	Ultra-High-Density Arrays of Defect-Free AlN Nanorods: A Space-Filling Approach. ACS Nano, 2016, 10, 1988-1994.	7.3	20
43	Exciton localization in polar and semipolar $(11\bar{2})$ $\text{In}_{0.2}\text{Ga}_{0.8}\text{N}$ /GaN multiple quantum wells. Semiconductor Science and Technology, 2016, 31, 085006.	1.0	7
44	GHz bandwidth semipolar $(11\bar{2})$ InGaIn/GaN light-emitting diodes. Optics Letters, 2016, 41, 5752.	1.7	40
45	InAlN high electron mobility transistor Ti/Al/Ni/Au Ohmic contact optimisation assisted by in-situ high temperature transmission electron microscopy. Applied Physics Letters, 2015, 107, 113506.	1.5	6
46	Semipolar $(20\bar{2})$ nitrides grown on $3\text{C-SiC}(001)$ Si substrates. Semiconductor Science and Technology, 2015, 30, 125007.	1.0	10
47	Semipolar (112) InGaIn light-emitting diodes grown on chemically-mechanically polished GaN templates. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2196-2200.	0.8	17
48	Plasmon-enhanced energy transfer in a hybrid system using silver nanobox array geometries. , 2015, , .		0
49	Plasmon-enhanced non-radiative energy transfer in a hybrid quantum well structure. , 2015, , .		0
50	Epitaxial lateral overgrowth of AlN on self-assembled patterned nanorods. Journal of Materials Chemistry C, 2015, 3, 431-437.	2.7	58
51	An enhanced surface passivation effect in InGaIn/GaN disk-in-nanowire light emitting diodes for mitigating Shockley-Read-Hall recombination. Nanoscale, 2015, 7, 16658-16665.	2.8	84
52	Over 20 MHz modulation bandwidth on 250 nm emission of AlGaIn micro-LEDs. Electronics Letters, 2015, 51, 354-355.	0.5	5
53	(Invited) Fully Porous GaN p-n Junctions Fabricated by Chemical Vapor Deposition: A Green Technology towards More Efficient LEDs. ECS Transactions, 2015, 66, 163-176.	0.3	1
54	Carrier density dependence of plasmon-enhanced nonradiative energy transfer in a hybrid quantum well-quantum dot structure. Optics Express, 2015, 23, 1377.	1.7	12

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55	MHz operation of 250 nm ultra-violet micro-light emitting diodes. , 2015, , .		0
56	250-nm emitting LED optimized for optical fibre coupling. , 2015, , .		1
57	Single phase (112Å ²) AlN grown on (101Å ⁰) sapphire by metalorganic vapour phase epitaxy. Journal of Crystal Growth, 2015, 414, 94-99.	0.7	26
58	Spectral analysis of In<inf>X</inf>Ga<inf>1âˆ”x</inf>N/GaN quantum well structures for III-nitride based solar cells. , 2014, , .		0
59	Influence of substrate miscut angle on surface morphology and luminescence properties of AlGaIn. Applied Physics Letters, 2014, 104, 092114.	1.5	24
60	Comparative study of polar and semipolar (112Å ²) InGaIn layers grown by metalorganic vapour phase epitaxy. Journal of Applied Physics, 2014, 116, 153505.	1.1	11
61	Electron Channeling Contrast Imaging of Defects in III-Nitride Semiconductors. Microscopy and Microanalysis, 2014, 20, 1024-1025.	0.2	0
62	Structural and optical properties of Ga auto-incorporated InAlIn epilayers. Journal of Crystal Growth, 2014, 408, 97-101.	0.7	19
63	Fully Porous GaN p-n Junction Diodes Fabricated by Chemical Vapor Deposition. ACS Applied Materials & Interfaces, 2014, 6, 17954-17964.	4.0	25
64	Determination of Ga auto-incorporation in nominal InAlIn epilayers grown by MOCVD. Journal of Materials Chemistry C, 2014, 2, 5787.	2.7	21
65	Enhanced UV luminescence from InAlIn quantum well structures using two temperature growth. Journal of Luminescence, 2014, 155, 108-111.	1.5	16
66	The effect of a varied NH ₃ flux on growth of AlN interlayers for InAlIn/GaN heterostructures. Applied Physics Letters, 2013, 103, 081602.	1.5	5
67	Composition-Dependent Band Gap and Band-Edge Bowing in AlInN: A Combined Theoretical and Experimental Study. Applied Physics Express, 2013, 6, 121001.	1.1	58
68	AlN heteroepitaxy on sapphire by metalorganic vapour phase epitaxy using low temperature nucleation layers. Journal of Crystal Growth, 2013, 383, 72-78.	0.7	37
69	Characterisation of III-nitride materials by synchrotron X-ray microdiffraction reciprocal space mapping. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 481-485.	0.8	5
70	Preparation of Substrates Intended for the Growth of Lower Threading Dislocation Densities within Nitride Based UV Multiple Quantum Wells. ECS Transactions, 2013, 53, 39-42.	0.3	2
71	Fabrication of p-type porous GaN on silicon and epitaxial GaN. Applied Physics Letters, 2013, 103, .	1.5	11
72	Rapid Nondestructive Analysis of Threading Dislocations in Wurtzite Materials Using the Scanning Electron Microscope. Physical Review Letters, 2012, 108, 135503.	2.9	56

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73	Imaging and identifying defects in nitride semiconductor thin films using a scanning electron microscope. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012, 209, 424-426.	0.8	16
74	Preface: <i>Phys. Status Solidi C</i> 3-4/2012. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 430-432.	0.8	0
75	Light Emitting and Laser Diodes in the Ultraviolet. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011, 17, 1402-1411.	1.9	21
76	The origin of the high ideality factor in AlGaIn-based quantum well ultraviolet light emitting diodes. <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 1761-1763.	0.7	30
77	Accurate ultra-low energy secondary ion mass spectrometry analysis of wide bandgap GaN/In _x Ga _{1-x} N structures using optical conductivity enhancement. <i>Rapid Communications in Mass Spectrometry</i> , 2010, 24, 2122-2126.	0.7	2
78	Crystal defect topography of Stranski-Krastanow quantum dots by atomic force microscopy. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	8
79	Characterization of gate recessed GaN/AlGaIn/GaN high electron mobility transistors fabricated using a SiCl ₄ /SF ₆ dry etch recipe. <i>Journal of Applied Physics</i> , 2010, 108, 013711.	1.1	9
80	Optical and microstructural study of a single layer of InGaIn quantum dots. <i>Journal of Applied Physics</i> , 2009, 105, 053505.	1.1	25
81	Comparison of damage introduced into GaN/AlGaIn/GaN heterostructures using selective dry etch recipes. <i>Semiconductor Science and Technology</i> , 2009, 24, 075020.	1.0	5
82	Low-Dimensional Waveguide Grating Fabrication in GaN with Use of SiCl ₄ /Cl ₂ /Ar-Based Inductively Coupled Plasma Dry Etching. <i>Journal of Electronic Materials</i> , 2009, 38, 635-639.	1.0	16
83	MOCVD growth and optical study of InGaIn quantum dots and their emitters on a high quality GaIn layer grown using a high temperature AlN as buffer. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S582-S585.	0.8	0
84	Optical spectroscopy of InGaIn-GaN quantum dot ensembles. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S586-S589.	0.8	0
85	Non-polar AlN and GaIn/AlN on α -plane sapphire. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S780.	0.8	10
86	Effect of the AlGaIn electron blocking layer thickness on the performance of AlGaIn-based ultraviolet light-emitting diodes. <i>Journal of Crystal Growth</i> , 2009, 311, 2857-2859.	0.7	20
87	In-Plane Optical Anisotropy of GaIn Refractive Index in Visible Light Region. <i>IEEE Photonics Technology Letters</i> , 2009, 21, 966-968.	1.3	10
88	Optical and microstructural studies of InGaIn/GaN quantum dot ensembles. <i>Applied Physics Letters</i> , 2009, 95, 111903.	1.5	7
89	Generation of misfit dislocations in highly mismatched GaIn/AlN layers. <i>Surface Science</i> , 2008, 602, 2643-2646.	0.8	15
90	Electron Channeling and Ion Channeling Contrast Imaging of Dislocations in Nitride Thin Films. <i>Microscopy and Microanalysis</i> , 2008, 14, 1194-1195.	0.2	2

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91	Growth and optical investigation of self-assembled InGaN quantum dots on a GaN surface using a high temperature AlN buffer. Journal of Applied Physics, 2008, 103, 123522.	1.1	41
92	The 310-340nm ultraviolet light emitting diodes grown using a thin GaN interlayer on a high temperature AlN buffer. Journal Physics D: Applied Physics, 2008, 41, 094003.	1.3	7
93	Temperature dependent behaviour of 340nm light emitting diodes incorporating a gallium nitride interlayer. Journal Physics D: Applied Physics, 2008, 41, 094004.	1.3	3
94	Influence of annealing temperature on optical properties of InGaN quantum dot based light emitting diodes. Applied Physics Letters, 2008, 93, .	1.5	21
95	Excitonic spin lifetimes in InGaN quantum wells and epilayers. Journal of Applied Physics, 2008, 104, 053523.	1.1	2
96	GaN hybrid microcavities in the strong coupling regime grown by metal-organic chemical vapor deposition on sapphire substrates. Journal of Applied Physics, 2007, 101, 093110.	1.1	20
97	Valence band offset of InN-AlN heterojunctions measured by x-ray photoelectron spectroscopy. Applied Physics Letters, 2007, 90, 132105.	1.5	89
98	Two coexisting mechanisms of dislocation reduction in an AlGaIn layer grown using a thin GaN interlayer. Applied Physics Letters, 2007, 91, 131903.	1.5	16
99	The influence of a capping layer on optical properties of self-assembled InGaN quantum dots. Journal of Applied Physics, 2007, 101, 113520-113520.	1.1	12
100	Room temperature operation of AlGaIn/GaN quantum well infrared photodetectors at a 3-4 μm wavelength range. Semiconductor Science and Technology, 2007, 22, 1240-1244.	1.0	9
101	Electron backscatter diffraction and electron channeling contrast imaging of tilt and dislocations in nitride thin films. Physical Review B, 2007, 75, .	1.1	69
102	Optical investigation of exciton localization in Al _x Ga _{1-x} N. Journal of Applied Physics, 2007, 101, 053513.	1.1	35
103	Phonon satellites and time-resolved studies of carrier recombination dynamics in InGaN quantum wells. Superlattices and Microstructures, 2007, 41, 419-424.	1.4	6
104	InGaIn/GaN quantum wells with low growth temperature GaN cap layers. Journal of Crystal Growth, 2007, 307, 363-366.	0.7	25
105	Improved AlN buffer layer technologies for UV-LEDs. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 120-124.	0.8	1
106	Inductively coupled plasma etching of GaN using SiCl ₄ /Cl ₂ /Ar for submicron-sized features fabrication. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2634-2637.	0.8	4
107	Investigations on Electrode-Less Wet Etching of GaN Using Continuous Ultraviolet Illumination. Journal of Electronic Materials, 2007, 36, 397-402.	1.0	14
108	Many-beam dynamical simulation of electron backscatter diffraction patterns. Ultramicroscopy, 2007, 107, 414-421.	0.8	166

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109	The influence of acceptor anneal temperature on the performance of InGaN/GaN quantum well light-emitting diodes. <i>Journal of Applied Physics</i> , 2006, 99, 024507.	1.1	6
110	Time-resolved photoluminescence studies of carrier diffusion in GaN. <i>Applied Physics Letters</i> , 2006, 89, 072107.	1.5	10
111	Dependence of carrier localization in InGaN ^x /GaN multiple-quantum wells on well thickness. <i>Applied Physics Letters</i> , 2006, 89, 253120.	1.5	35
112	Time Evolution of the Screening of Piezoelectric Fields in InGaN Quantum Wells. <i>IEEE Journal of Quantum Electronics</i> , 2006, 42, 1202-1208.	1.0	47
113	Optical properties of AlGaIn ^x /GaN multiple quantum well structure by using a high-temperature AlN buffer on sapphire substrate. <i>Journal of Applied Physics</i> , 2006, 99, 023513.	1.1	27
114	The role of vacancies in the red luminescence from Mg-doped GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1919-1922.	0.8	11
115	The magnesium acceptor states in GaN: an investigation by optically-detected magnetic resonance. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1892-1896.	0.8	0
116	Stimulated emission and carrier dynamics in AlInGaIn multi-quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1958-1961.	0.8	0
117	Fast spin relaxation in InGaIn/GaN multiple quantum wells. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 1643-1646.	0.7	1
118	V-shaped pits formed at the GaN/AlN interface. <i>Journal of Crystal Growth</i> , 2006, 289, 63-67.	0.7	20
119	Characterisation of nitride thin films by electron backscatter diffraction and electron channelling contrast imaging. <i>Materials Science and Technology</i> , 2006, 22, 1352-1358.	0.8	4
120	Resolution of discrete excited states in In _x Ga _{1-x} N multiple quantum wells using degenerate four-wave mixing. <i>Physical Review B</i> , 2006, 73, .	1.1	10
121	Effects of depletion on the emission from individual InGaIn dots. <i>Applied Physics Letters</i> , 2006, 88, 122115.	1.5	3
122	Optically-detected magnetic resonance of spin-paired complexes emitting in the 2.3 eV spectral region in Mg-doped GaN. <i>Physical Review B</i> , 2006, 74, .	1.1	4
123	Origin of the red luminescence in Mg-doped GaN. <i>Applied Physics Letters</i> , 2006, 89, 022107.	1.5	28
124	Greatly improved performance of 340 nm light emitting diodes using a very thin GaN interlayer on a high temperature AlN buffer layer. <i>Applied Physics Letters</i> , 2006, 89, 081126.	1.5	31
125	Mechanisms of dislocation reduction in an Al _{0.98} Ga _{0.02} N layer grown using a porous AlN buffer. <i>Applied Physics Letters</i> , 2006, 89, 131925.	1.5	17
126	The role of acceptor anneal temperature on the performance of InGaIn/GaN quantum well light emitting diodes. , 2005, , .		0

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127	A study of dislocations in AlN and GaN films grown on sapphire substrates. Journal of Crystal Growth, 2005, 282, 290-296.	0.7	75
128	Microphotoluminescence and photocurrent studies of InGaN quantum dots grown by MOVPE at low surface densities on GaN. Microelectronics Journal, 2005, 36, 223-226.	1.1	0
129	AlGaIn-based Bragg mirrors and hybrid microcavities for the ultra-violet spectral region. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 813-816.	0.8	8
130	Picosecond carrier dynamics in AlInGaIn multiple quantum wells. Applied Physics Letters, 2005, 87, 232106.	1.5	4
131	Fabrication and optical investigation of a high-density GaN nanowire array. Applied Physics Letters, 2005, 86, 103103.	1.5	33
132	Nature of acceptor states in magnesium-doped gallium nitride. Physical Review B, 2005, 71, .	1.1	16
133	Air-bridged lateral growth of an Al _{0.98} Ga _{0.02} N layer by introduction of porosity in an AlN buffer. Applied Physics Letters, 2005, 87, 151906.	1.5	49
134	Effect of strain relaxation and exciton localization on performance of 350-nm AlInGaIn quaternary light-emitting diodes. Journal of Applied Physics, 2005, 97, 083104.	1.1	13
135	Pressure-dependent photoluminescence study of epitaxial AlGaIn to 19 GPa. Semiconductor Science and Technology, 2004, 19, L22-L24.	1.0	0
136	Optical investigation of InGaIn-GaN multiple-quantum wells under high excitation. Applied Physics Letters, 2004, 84, 5159-5161.	1.5	15
137	High-reflectivity Al _x Ga _{1-x} N/Al _y Ga _{1-y} N distributed Bragg reflectors with peak wavelength around 350nm. Applied Physics Letters, 2004, 85, 43-45.	1.5	32
138	Femtosecond studies of electron capture times in InGaIn/GaN multiple quantum wells. Applied Physics Letters, 2004, 84, 3052-3054.	1.5	14
139	Influence of dual-frequency plasma-enhanced chemical-vapor deposition Si ₃ N ₄ passivation on the electrical characteristics of AlGaIn/GaN heterostructure field-effect transistors. Journal of Electronic Materials, 2004, 33, 400-407.	1.0	24
140	Highly improved performance of a 350nm ultraviolet light-emitting diode containing Al _x Ga _{1-x} N/Al _y Ga _{1-y} N distributed Bragg reflectors. Journal of Crystal Growth, 2004, 267, 583-587.	0.7	8
141	Study of stimulated emission from InGaIn/GaN multiple quantum well structures. Journal of Crystal Growth, 2004, 273, 48-53.	0.7	8
142	Raman scattering and absorption study of the high-pressure wurtzite to rocksalt phase transition of GaN. Physical Review B, 2004, 69, .	1.1	49
143	Orientation of cracks in AlGaIn epilayers with sapphire substrates. Journal of Materials Science Letters, 2003, 22, 113-114.	0.5	2
144	Electrical characteristics of AlGaIn/GaN metal-insulator semiconductor heterostructure field-effect transistors on sapphire substrates. Journal of Electronic Materials, 2003, 32, 350-354.	1.0	7

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145	Effect of anneal temperature on GaN nucleation layer transformation. Journal of Crystal Growth, 2003, 258, 89-99.	0.7	31
146	Carrier capture times in InGaN/GaN multiple quantum wells. Physica Status Solidi (B): Basic Research, 2003, 240, 364-367.	0.7	10
147	Electronic Raman scattering from intersubband transitions in GaN/AlGaIn quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2662-2665.	0.8	1
148	MOCVD growth and optical investigation of the AlInGaIn quaternary system. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2019-2022.	0.8	7
149	Compositional analysis of AlInGaIn quaternary layers grown by metalorganic vapour phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2478-2481.	0.8	9
150	Photoluminescence of single InGaIn quantum dots grown at low surface densities by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2721-2724.	0.8	4
151	Crack formation and development in AlGaIn/GaN structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2055-2058.	0.8	7
152	Direct, Independent Measurement of Twist and Tilt Mosaic as a Function of Thickness in Epitaxial GaIn. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 542-545.	0.8	9
153	Influence of alloy composition and interlayer thickness on twist and tilt mosaic in Al _x Ga _{1-x} N/AlIn/GaN heterostructures. Applied Physics Letters, 2003, 83, 5434-5436.	1.5	19
154	Crack initiation and termination in III-V epitaxial layers. Philosophical Magazine, 2003, 83, 3077-3092.	0.7	3
155	Metastable rocksalt phase in epitaxial GaIn on sapphire. Applied Physics Letters, 2003, 83, 2808-2810.	1.5	5
156	Electron-beam-induced segregation in InGaIn/GaN multiple-quantum wells. Applied Physics Letters, 2003, 83, 1965-1967.	1.5	70
157	Effect of Si doping on the relaxation mechanism of InGaAs on GaAs. Applied Physics Letters, 2002, 81, 2773-2775.	1.5	9
158	Influence of premetallization surface treatment on the formation of Schottky Au-nGaIn contacts. Journal of Applied Physics, 2002, 92, 3179-3186.	1.1	28
159	Influence of GaIn barrier growth temperature on the photoluminescence of InGaIn/GaN heterostructures. Journal Physics D: Applied Physics, 2002, 35, 599-603.	1.3	25
160	Comparison of different surface passivation dielectrics in AlGaIn/GaN heterostructure field-effect transistors. Journal Physics D: Applied Physics, 2002, 35, 595-598.	1.3	69
161	Crack Nucleation in AlGaIn/GaN Heterostructures. Materials Research Society Symposia Proceedings, 2002, 743, L7.10.1.	0.1	1
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